

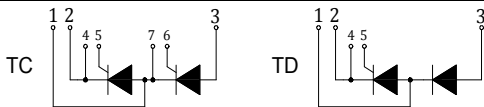
Key Parameters

V_{RRM}	1400	V
$I_{T(AV)}$	700	A
I_{TSM}	21	kA
V_{TO}	0.85	V
r_T	0.22	mΩ

Applications

- Various rectifiers
- DC supply for PWM inverter
- Industry converter

- 3000 V_{RMS} isolating voltage with baseplate
- High power capability
- Industrial standard package


Voltage Ratings

Module Type	$V_{DRM}/V_{RRM}(V)$	Test Conditions
TMTC 700	1400	$T_{vj} = 25, 130\text{ °C}$ $I_{DRM} = I_{RRM} \leq 150\text{ mA}$ $V_{DM} = V_{DRM}$ $V_{RM} = V_{RRM}$ $t_p = 10\text{ ms}$ $V_{DSM} = V_{DRM}$ $V_{RSM} = V_{RRM} + 100$


Thermal & Mechanical Data

Symb.	Parameter	Test Conditions	Min	Type	Max	Unit
$R_{th(J-C)}$	Thermal Resistance junction to case	sine.180°, per chip / per module DC , per chip / per module	-	-	0.064 / 0.032 0.061/ 0.03	K / W
$R_{th(C-H)}$	Thermal resistanc case to heatsink	per chip / per module	-	-	0.02 / 0.01	K / W
T_{vj}	Maximum junction temperature		-	-	135	°C
$T_{c op}$	operating temperature		-40	-	130	°C
T_{stg}	Storage temperature		-40	-	130	°C
F	Busbar to module M10 Module to heatsink M6	Mounting torque $\pm 10\%$	-	12 6	-	N·m N·m
W	Weight		-	1.5	-	kg
S	Creepage distance		-	19	-	mm
a	vibration resistance		-	50	-	m/s ²

Current Ratings

Symb.	Parameter	Test Conditions	Min	Type	Max	Unit
$I_{T(AV)}$	Mean on-state current	Half Sine Wave, $T_C=85\text{ °C}$ Half Sine Wave, $T_C=80\text{ °C}$	-	-	650 703	A
$I_{T(RMS)}$	RMS on-state current	$T_C=85\text{ °C}$	-	-	1021	A
I_{TSM}	Surge on-state current	$t_p=10\text{ms}$, Half Sine Wave, $T_{vj}=25\text{ °C}$, $V_R=0$	-	-	21.0	kA
I^2t	Limiting load integral	Sine Wave, $t_p=10\text{ms}$	-	-	221	$10^4\text{ A}^2\text{s}$

Characteristics

Symb.	Parameter	Test Conditions	Min	Type	Max	Unit
V_{TM}	Peak on-state voltage	$T_{vj} = 25^{\circ}\text{C}$, $I_{TM} = 1950\text{ A}$ $T_{vj} = 130^{\circ}\text{C}$, $I_{TM} = 1950\text{ A}$	-	-	1.4 1.34	V
I_{DRM}	Forward leakage current	$T_{vj} = 25^{\circ}\text{C}$, 130°C , V_{DRM}/V_{RRM}	-	-	150	mA
I_{RRM}	Reverse leakage current		-	-	-	-
V_{isol}	Isolation voltage	a.c.; 50 Hz; r.m.s.; t=1min	-	3000	-	V
V_{TO}	Threshold voltage	$T_{vj} = 130^{\circ}\text{C}$	-	-	0.85	V
r_T	Slope resistance	$T_{vj} = 130^{\circ}\text{C}$	-	-	0.22	m Ω
I_H	Holding current	$T_{vj} = 25^{\circ}\text{C}$	-	-	200	mA
I_L	Latching current	$T_{vj} = 25^{\circ}\text{C}$	-	-	1000	mA

Dynamic Parameters

Symb.	Parameter	Test Conditions	Min	Type	Max	Unit
dv/dt	Critical rate of rise of off-state voltage	$T_{vj} = 130^{\circ}\text{C}$, Exp. to $0.67 V_{DRM}$	1000	-	-	V/ μs
di/dt	Critical rate of rise of on-state current	$T_{vj} = 130^{\circ}\text{C}$, $V_{DM} = 0.67 V_{DRM}$, $f = 50\text{ Hz}$ $I_{TM} = 1000\text{ A}$, $I_{FG} = 2\text{ A}$, $t_r = 0.5\text{ }\mu\text{s}$	-	-	250	A/ μs
t_q	Turn-off time	$T_{vj} = 130^{\circ}\text{C}$, $V_{DM} = 0.67 V_{DRM}$, $I_T = I_{TMAX}$ $dv/dt = 20\text{ V}/\mu\text{s}$, $V_R = 200\text{ V}$, $-di/dt = 10\text{ A}/\mu\text{s}$	-	150	-	μs
Q_{rr}	Reverse Recovery Charge	$T_{vj} = 130^{\circ}\text{C}$, $-di/dt = 10\text{ A}/\mu\text{s}$, $I_T = I_{TM}$, $V_R = 200\text{ V}$	-	1000	-	μC

Gate Parameters

Symb.	Parameter	Test Conditions	Min	Type	Max	Unit
I_{GT}	Gate trigger current	$T_{vj} = 25^{\circ}\text{C}$	200	-	-	mA
V_{GT}	Gate trigger voltage	$T_{vj} = 25^{\circ}\text{C}$	-	-	3	V
V_{GD}	Gate non-trigger voltage	$T_{vj} = 130^{\circ}\text{C}$, $V_D = 0.4V_{DRM}$	0.3	-	-	V
V_{FGM}	Peak forward gate voltage		-	-	12	V
V_{RGM}	Peak reverse gate voltage		-	-	5	V
P_{GM}	Gate peak power losses		-	-	20	W
$P_{G(AV)}$	Gate average power losses		-	-	4	W

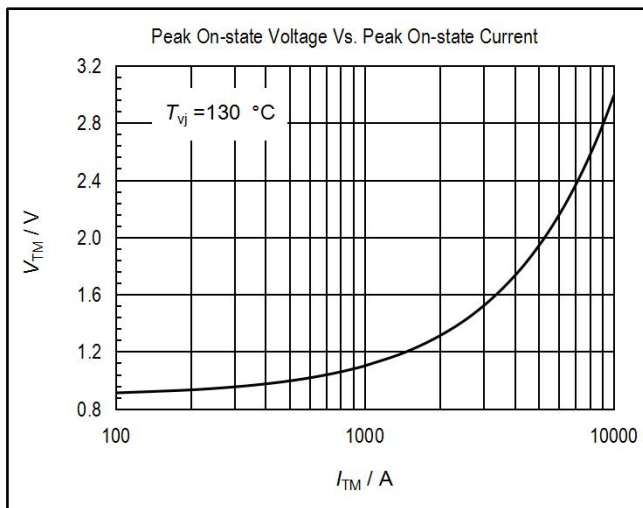


Fig1. Peak on-state Voltage Vs. Peak On-state Current

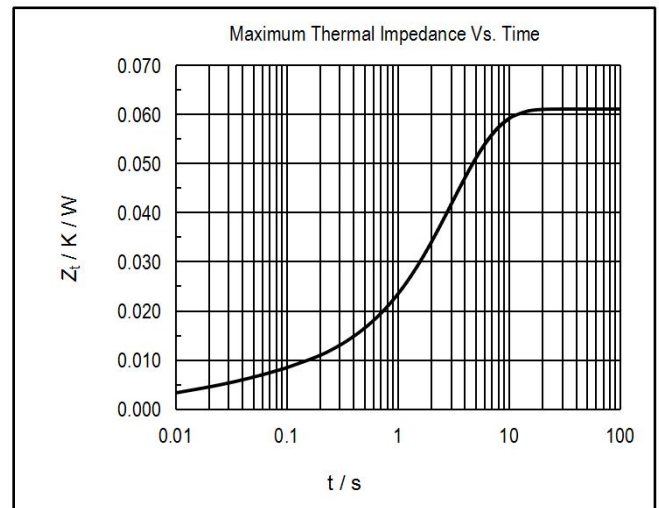


Fig2. Transient thermal Impedance Vs. Time

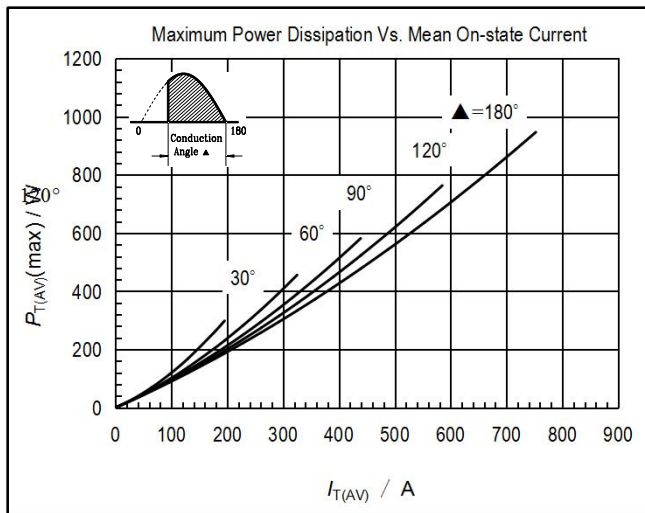


Fig3. Maximum Power Dissipation Vs. Mean On-state Current

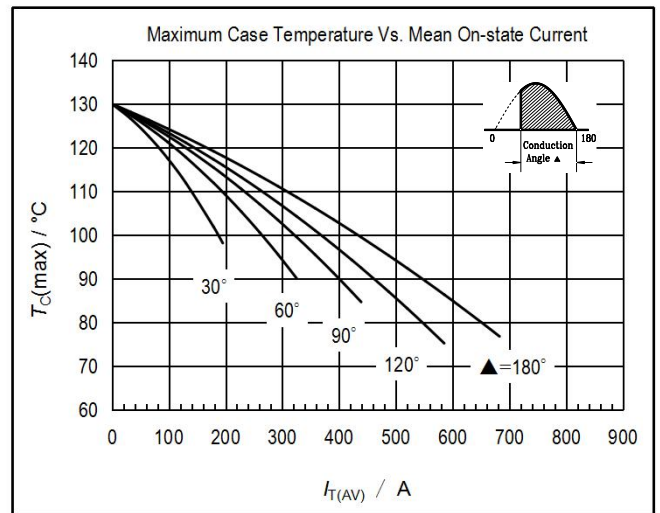


Fig4. Maximum Case Temperature Vs. Mean On-state Current

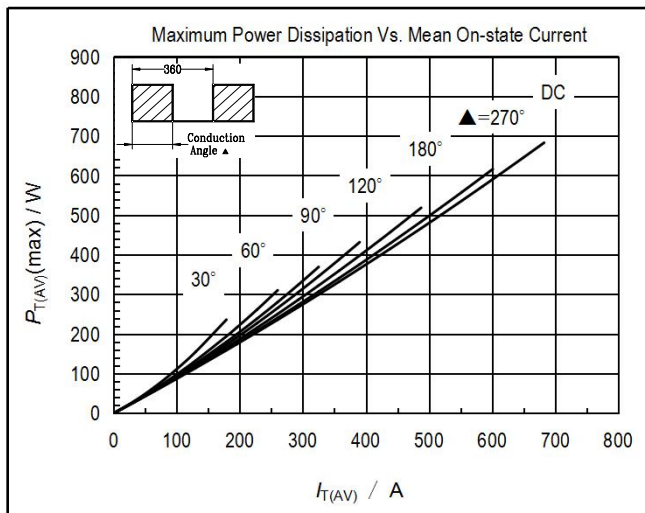


Fig5. Maximum Power Dissipation Vs. Mean On-state Current

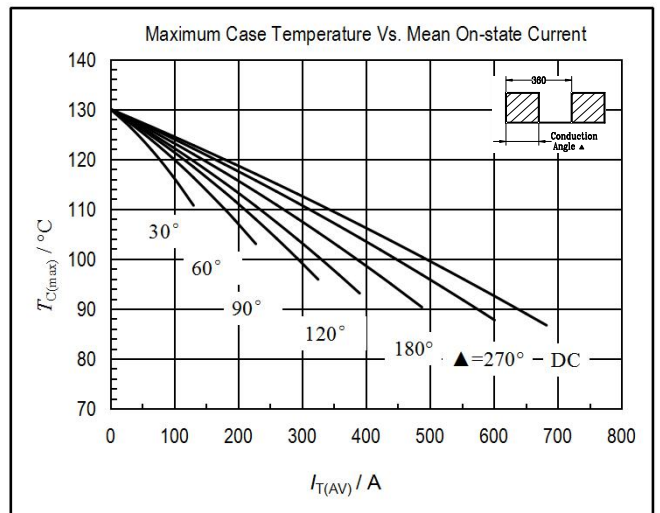


Fig6. Maximum Case Temperature Vs. Mean On-state Current

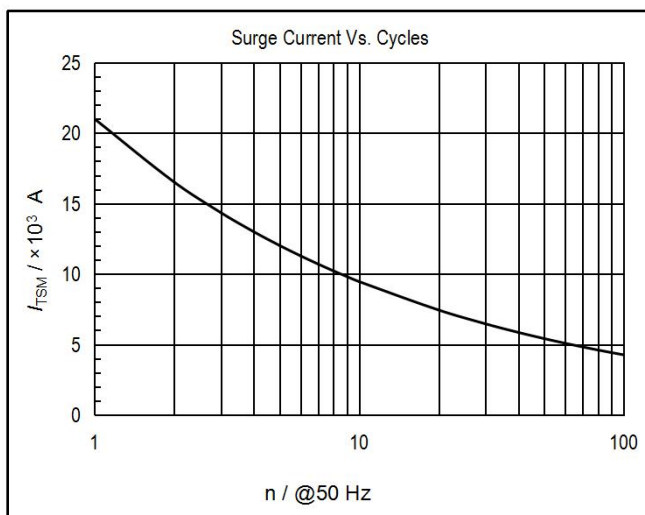


Fig7. Surge Current Vs. Cycles

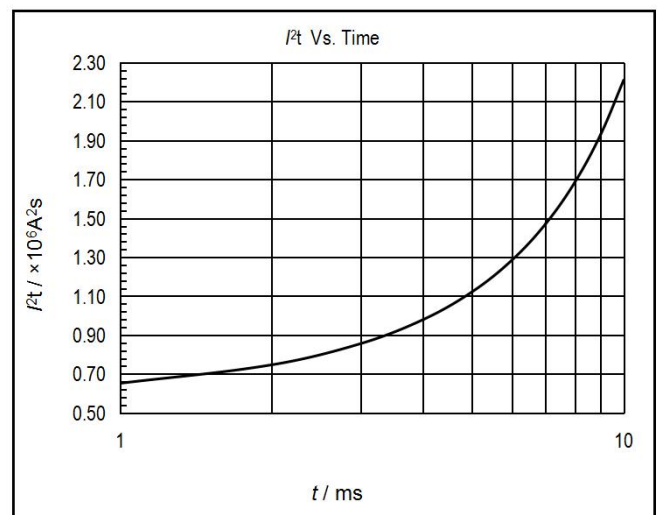


Fig8. I^2t Vs. Time

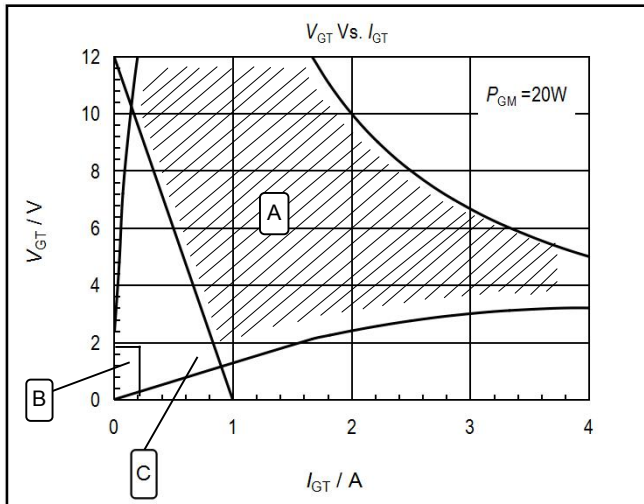


Fig9. V_{GT} Vs. I_{GT}

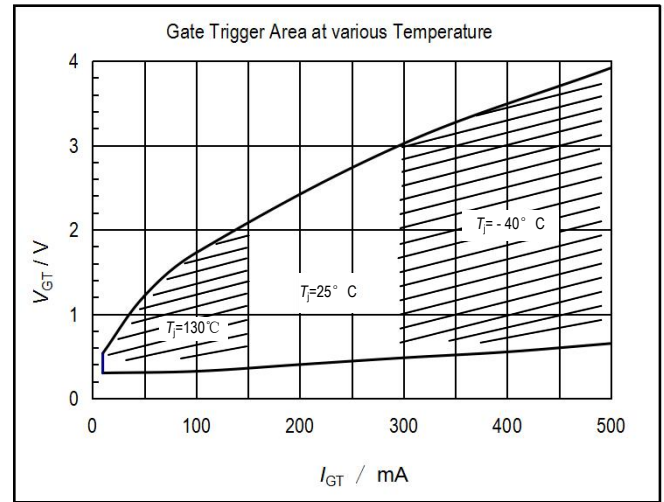


Fig10. Gate Trigger Area at various Temperature

A is Recommended Triggering Area.
B is Unreliable Triggering Area.
C is Recommended Gate Load Line.

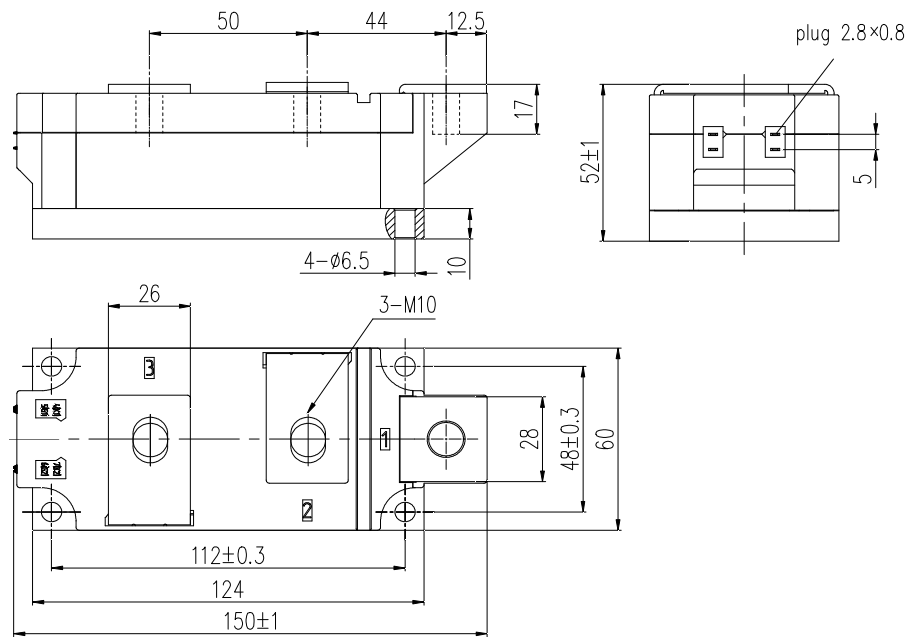


Fig9.Outline

株洲中车时代半导体有限公司

ZHUZHOU CRRC TIMES SEMICONDUCTOR Co., LTD.

Address Tianxin, ZhuZhou City, Hunan Province, China

Zipcode 412001

Telephone 0731 - 28498268, 28498124

Fax 0731 - 28498851, 28498494

Email sbu@crzczic.cc

Web Site www.sbu.crzczic.cc